
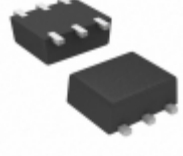

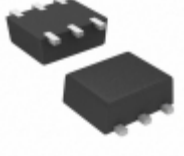

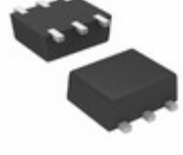
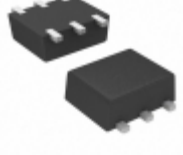
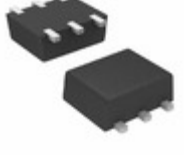

	<h2 style="color: red;">SI1072X-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI1072X-T1-GE3</p> <hr/> <p>Hersteller / Marke: Vishay / Siliconix</p> <hr/> <p>Teil der Beschreibung: MOSFET N-CH 30V SC89</p> <hr/> <p>Datenblätter:  SI1072X-T1-GE3.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 99000 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1072X-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 30V SC89
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	99000 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SC-89-6
Verlustleistung (max)	236mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	-
Rds On (Max) @ Id, Vgs	93 mOhm @ 1.3A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	8.3nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	280pF @ 15V
Verpackung	Tape & Reel (TR)


















































SI1072X-T1-GE3 ist neu im Original, Suche SI1072X-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1072X-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1072X-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1073X-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 0.98A SC89-6</p>	 <p>SI1072X-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V SC89</p>	 <p>SI1071X-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 0.96A SC89-6</p>	 <p>SI1073X-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 0.98A SC89-6</p>
 <p>SI1071X-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 0.96A SC89-6</p>	 <p>SI1071X-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 0.96A SOT563F</p>	 <p>SI1072X-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 1.3A SOT563F</p>	 <p>SI1073X-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 0.98A SC89-6</p>

heiße Teile

Mehr

 SI1056X-T1-E3	 SI1056X-T1-GE3	 SI1056X-T1-GE3	 SI1058X-T1-GE3	 SI1058X-T1-GE3
 SI1065X-T1-E3	 SI1065X-T1-E3	 SI1065X-T1-GE3	 SI1065X-T1-GE3	 SI1067X-T1-E3
 SI1067X-T1-E3	 SI1067X-T1-GE3	 SI1067X-T1-GE3	 SI1069X-T1-E3	 SI1069X-T1-E3
 SI1069X-T1-GE3	 SI1069X-T1-GE3	 SI1070X-T1-E3	 SI1070X-T1-E3	 SI1070X-T1-GE3
 SI1070X-T1-GE3	 SI1071X-T1-GE3	 SI1071X-T1-GE3	 SI1072X-T1-E3	 SI1072X-T1-E3
 SI1072X-T1-GE3	 SI1073X-T1-GE3	 SI1073X-T1-GE3	 SI1120-A-GMR	 SI1132-A10-GMR
 SI1133-AA00-GMR	 SI113DP-T1-GE3	 SI1141-A10-GMR	 SI1142-A11-GMR	 SI1143-A11-GMR
 SI1143-M01-GMR	 SI1144-AAGX-GMR	 SI1300BDL-T1-E3	 SI1300BDL-T1-E3	 SI1300BDL-T1-GE3
 SI1300BDL-T1-GE3	 SI1300DL	 SI1300DL-T1	 SI1300DL-T1-GE3	 SI1301DL
 SI1301DL-T1	 SI1301DL-T1-E3	 SI1301DL-T1-GE3	 SI1301DL-T1/LGW	 SI1302DL

Contact us: Info@Y-IC.com

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